

## PSMN4R5-30YLC

# N-channel 30 V 4.8 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 5 July 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, QOSS for high system efficiencies at low and high loads

## 1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing

- Server power supplies
- Sync rectifier

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	84	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2	-	-	61	W
T <sub>j</sub>	junction temperature		-55	-	175	°C
Static cha	racteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	5.1	6.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A};$ $T_i = 25 \text{ °C}; \text{ see Figure 12}$	-	4	4.8	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic c	haracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 4.5 V; $I_D$ = 20 A; $V_{DS}$ = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.85	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 4.5 V; $I_D$ = 20 A; $V_{DS}$ = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9.6	-	nC

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	[Q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 \$
			SOT669 (LFPAK; Power-SO8)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R5-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PSMN4R5-30YLC	4C530L

<sup>[1] % =</sup> placeholder for manufacturing site code.

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$25 \text{ °C} \le T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	60	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	84	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4	-	334	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	61	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	270	-	V
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	55	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	334	Α
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 84 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped; see Figure 3	-	14.5	mJ

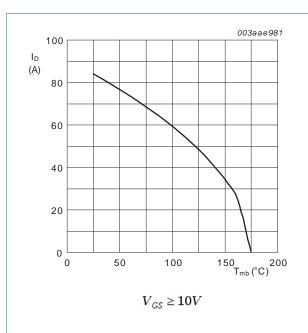


Fig 1. Continuous drain current as a function of mounting base temperature

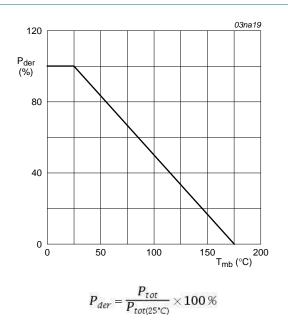
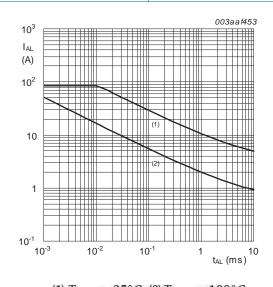
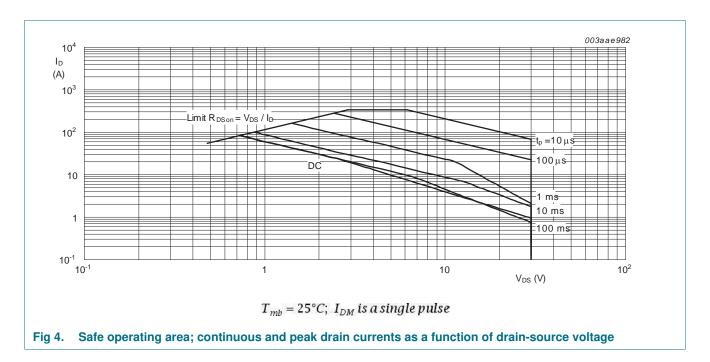


Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1)  $T_{j(init)} = 25^{\circ}C$ ; (2)  $T_{j(init)} = 100^{\circ}C$ 

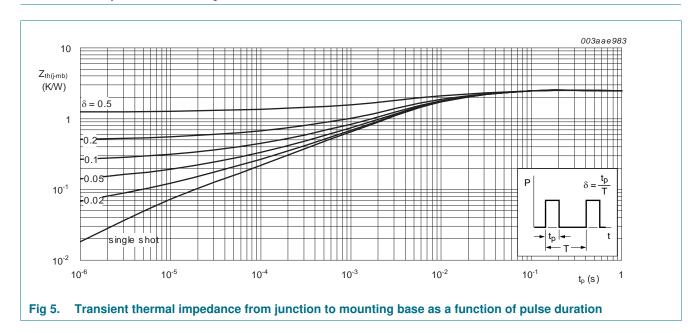
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	2.26	2.48	K/W



## 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 10	1.05	1.54	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	5.1	6.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	11	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	4	4.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 °C;$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	8.6	mΩ
$R_G$	gate resistance	f = 1 MHz	-	2.1	4.2	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	20.5	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	9.6	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	18.5	-	nC
$Q_{GS}$	gate-source charge	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;	-	3.2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	1.14	-	nC
$Q_{GD}$	gate-drain charge		-	2.85	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 20 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see Figure 14; see Figure 15	-	2.74	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1324	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	288	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	97	-	pF

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.75 \Omega;$	-	17.2	-	ns
t <sub>r</sub>	rise time	$V_{GS} = 4.5 \text{ V}; R_{G(ext)} = 4.7 \Omega$	-	18.7	-	ns
$t_{d(off)}$	turn-off delay time		-	24.3	-	ns
t <sub>f</sub>	fall time		-	8.75	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	7.9	-	nC
Source-drain	diode					
V <sub>SD</sub>	source-drain voltage	$I_S$ = 20 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu s;$	-	29.8	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	27.8	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A};$ $dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{DS} = 15 \text{ V};$ see Figure 18	-	18.8	-	ns
t <sub>b</sub>	reverse recovery fall time		-	11	-	ns

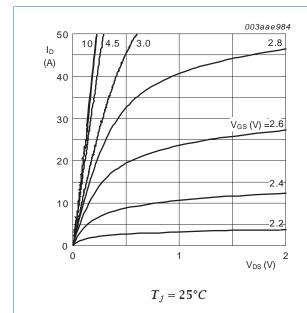


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

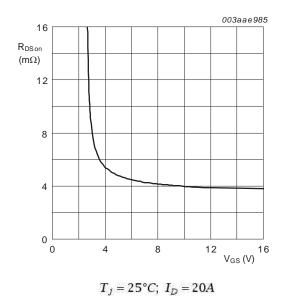


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

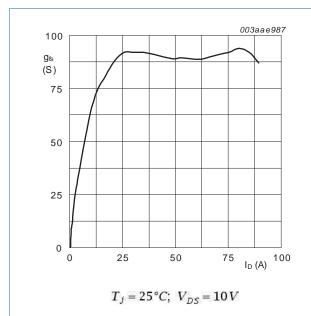


Fig 8. Forward transconductance as a function of drain current; typical values

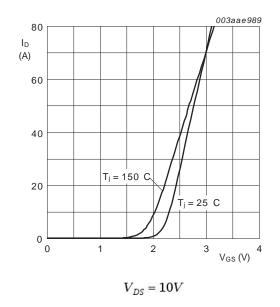


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

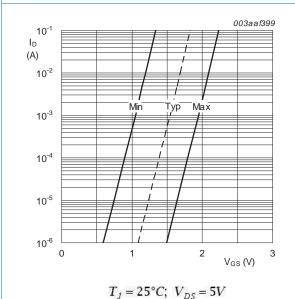


Fig 10. Sub-threshold drain current as a function of gate-source voltage

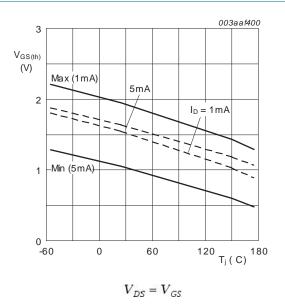


Fig 11. Gate-source threshold voltage as a function of junction temperature

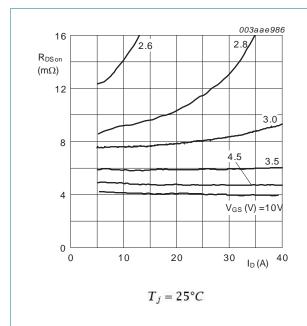


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

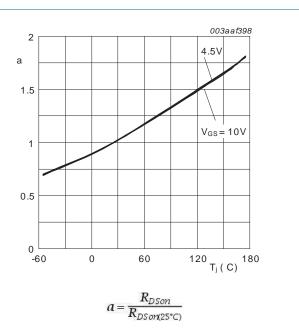


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

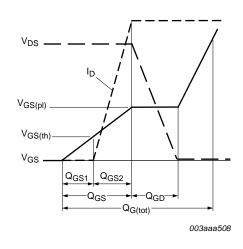
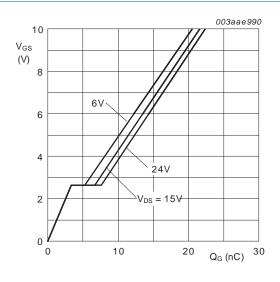


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; I_D = 20A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

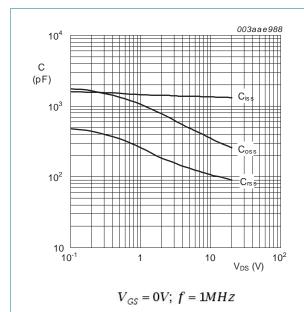


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

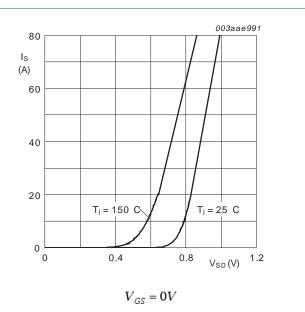


Fig 17. Source current as a function of source-drain voltage; typical values

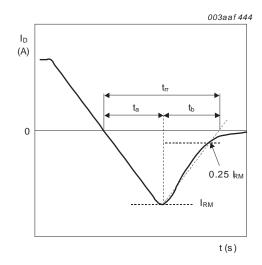


Fig 18. Reverse recovery timing definition

## **Package outline**



**SOT669** 

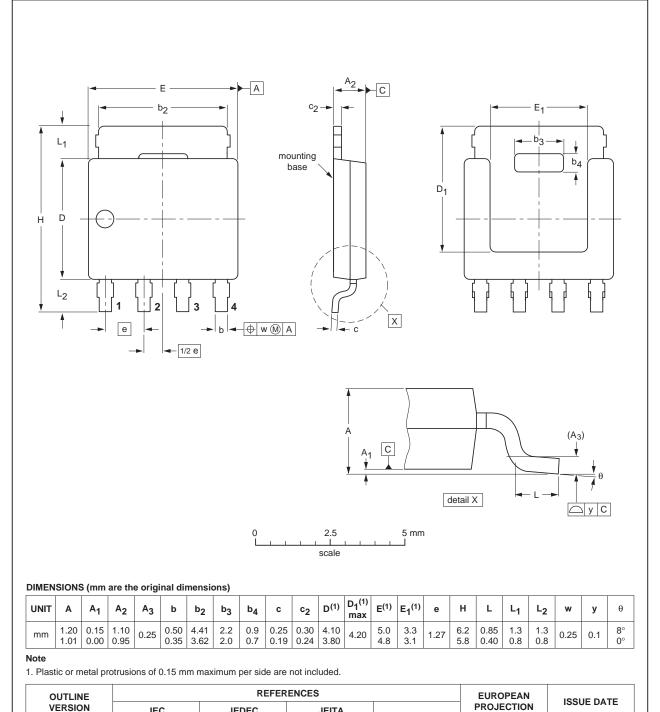


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

**JEDEC** 

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PSMN4R5-30YLC

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SOT669

## 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R5-30YLC v.3	20110705	Product data sheet	-	PSMN4R5-30YLC v.2
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
PSMN4R5-30YLC v.2	20101130	Product data sheet	-	PSMN4R5-30YLC v.1

## 10. Legal information

#### 10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN4R5-30YLC

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## PSMN4R5-30YLC

## N-channel 30 V 4.8 m $\Omega$ logic level MOSFET in LFPAK using NextPower

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## PSMN4R5-30YLC

## **Nexperia**

N-channel 30 V 4.8 m $\Omega$  logic level MOSFET in LFPAK using NextPower

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